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THIRD SERIES, VOLUME 58, NUMBER 23

CONTENTS

15 DECEMBER 1998-I

BRIEF REPORTS

Electronic structure: wide-band, narrow-band, and strongly correlated systems

- Long-wavelength optical phonons in ternary nitride-based crystals 15 283
SeGi Yu, K. W. Kim, Leah Bergman, Mitra Dutta, Michael A. Stroscio, and John M. Zavada
- Magnetic and charge correlations of the two-dimensional t - t' - U Hubbard model 15 288
Raymond Frésard and Walter Zimmermann
- Electronic dielectric constants of insulators calculated by the polarization method 15 292
Fabio Bernardini and Vincenzo Fiorentini
- Energy renormalization-group method for electronic structure of large systems 15 296
Roi Baer and Martin Head-Gordon
- LDA exchange-energy functional 15 300
Antonis N. Andriotis
- Electronic structure of indium nitride studied by photoelectron spectroscopy 15 304
Q. X. Guo, M. Nishio, H. Ogawa, A. Wakahara, and A. Yoshida
- Ab initio* studies of the structural and electronic properties of solid cubane 15 307
Steven L. Richardson and José Luis Martins
- Dynamical mean-field solution for a model of metal-insulator transitions in moderately doped manganites 15 310
F. Zhong, J. Dong, and Z. D. Wang
- Collapse of the charge gap in random Mott insulators 15 314
Y. Otsuka, Y. Morita, and Y. Hatsugai
- $3e$ tunneling processes in a superconducting single-electron tunneling transistor 15 317
P. Hadley, E. Delvigne, E. H. Visscher, S. Lähteenmäki, and J. E. Mooij
- Nonadiabatic scattering of a classical particle in an inhomogeneous magnetic field 15 321
F. Evers, A. D. Mirlin, D. G. Polyakov, and P. Wölflé

Semiconductors I: bulk

- Approximate *ab initio* calculation of vibrational properties of hydrogenated amorphous silicon
with inner voids 15 325
Serge M. Nakhmanson and D. A. Drabold
- Exciton binding energy in the strong correlation limit of conjugated chains 15 329
Z. Shuai, J. L. Brédas, S. K. Pati, and S. Ramasesha
- State of Mott minimal metallic conductivity in a scaling approach to the metal-insulator transition in doped
semiconductors 15 333
I. Shlimak and M. Kaveh
- Dynamic theory of excitonic hyper-Raman gain 15 336
K. Hannewald, S. Glutsch, and F. Bechstedt



Second-order susceptibility from a tight-binding Hamiltonian	15 340
T. Dumitrică, J. S. Graves, and R. E. Allen	
Model for energy transfer from porous silicon nanocrystallites to SiH surface vibrations at low temperature	15 344
S. Létant and G. Fishman	
Semiconductors II: surfaces, interfaces, microstructures, and related topics	
Domain boundaries on {1120} planes in GaN: A theoretical study	15 347
J. Elsner, M. Kaukonen, M. I. Heggie, M. Haugk, Th. Frauenheim, and R. Jones	
Local strain in interface: Origin of grain tilting in diamond (001)/silicon (001) heteroepitaxy	15 351
X. Jiang, R. Q. Zhang, G. Yu, and S. T. Lee	
X-ray diffraction and excitation photoluminescence analysis of ordered GaInP	15 355
R. L. Forrest, T. D. Golding, S. C. Moss, Z. Zhang, J. F. Geisz, J. M. Olson, A. Mascarenhas, P. Ernst, and C. Geng	
Smooth growth fronts in Si/Ge heteroepitaxy by kinetic growth manipulation	15 359
Wulf Wulfhekkel, Harold J. W. Zandvliet, Bart-Jan Hattink, Georg Rosenfeld, George Comsa, and Bene Poelsema	
Scaling relations for gaps in fractional quantum Hall states	15 363
Ganpathy Murthy, K. Park, R. Shankar, and J. K. Jain	
Polariton-induced optical asymmetry in semiconductor microcavities	15 367
A. Armitage, M. S. Skolnick, A. V. Kavokin, D. M. Whittaker, V. N. Astratov, G. A. Gehring, and J. S. Roberts	
Shot noise in diffusive conductors: A quantitative analysis of electron-phonon interaction effects	15 371
Y. Naveh, D. V. Averin, and K. K. Likharev	
Spin splitting in the electron subband of asymmetric GaAs/Al _x Ga _{1-x} As quantum wells: The multiband envelope function approach	15 375
L. Wissinger, U. Rössler, R. Winkler, B. Jusserand, and D. Richards	
Interface-induced suppression of the Auger recombination in type-II InAs/GaSb superlattices	15 378
H. Mohseni, V. I. Litvinov, and M. Razeghi	
Electronic states of V-shaped semiconductor quantum wires in electric fields	15 381
Hong Sun	
Photoluminescence from a modulation-doped Al _{0.33} Ga _{0.67} As/GaAs heterointerface under cyclotron resonance	15 385
K. Suzuki, K. Saito, K. Muraki, and Y. Hirayama	
Dynamic confinement of electrons in time-dependent quantum structures	15 389
Chang Sub Kim and Arkady M. Satanin	
Self-consistent analysis of a quantum capacitor	15 393
Pawel Pomorski, Hong Guo, R. Harris, and Jian Wang	
Spin-dependent electronic tunneling at zero magnetic field	15 397
A. Voskoboynikov, Shiue Shin Liu, and C. P. Lee	
Universality in the crossover between edge-channel and bulk transport in the quantum Hall regime	15 401
J. Oswald, G. Span, and F. Kuchar	
Raman spectroscopy of PbS nanocrystalline semiconductors	15 405
K. K. Nanda, S. N. Sahu, R. K. Soni, and S. Tripathy	
Charged excitons trapped on monomolecular CdTe islands in wide ZnTe-(Zn,Mg)Te quantum wells	15 408
Thierry Taliercio, Pierre Lefebvre, Vincent Calvo, Denis Scalbert, Noël Magnea, Henry Mathieu, and Jacques Allègre	
Surface physics, low-dimensional systems, and related topics	
Structure and stability of finite gold nanowires	15 412
G. Bilalbegović	

Exact determination of the phase in neutron reflectometry by variation of the surrounding media	15 416
C. F. Majkrzak and N. F. Berk	
Surface-plasmon-enhanced transmission through metallic gratings	15 419
U. Schröter and D. Heitmann	
Reversed spin polarization at the Co(001)-HfO ₂ (001) interface	15 422
P. K. de Boer, G. A. de Wijs, and R. A. de Groot	
Photoelectron diffraction in magnetic dichroism: Surface live magnetic layers in fcc Fe/Co(001)	15 426
Xingyu Gao, M. Salvietti, W. Kuch, C. M. Schneider, and J. Kirschner	
Photon-induced anion emission: A mechanism for ion-induced secondary-electron emission from an Al/O surface	15 430
S. G. Walton, B. L. Peko, and R. L. Champion	

ARTICLES

Electronic structure: wide-band, narrow-band, and strongly correlated systems

Electronic and phonon properties of six crystalline phases of Pu metal	15 433
Duane C. Wallace	
<i>T</i> -asymmetry signals originating from magnetic order through the double-exchange mechanism	15 440
H. C. Ren and M. K. Wu	
Fermion loops, loop cancellation, and density correlations in two-dimensional Fermi systems	15 449
Arne Neumayr and Walter Metzner	
Correlation energy of an electron gas in strong magnetic fields at high densities	15 460
M. Steinberg and J. Ortner	
Dynamical properties of a two-dimensional electron gas in a magnetic field within the composite fermion model ..	15 468
Darren J. T. Leonard and Neil F. Johnson	
Tunneling spectroscopy on the correlation effects in FeSi	15 483
M. Fäth, J. Aarts, A. A. Menovsky, G. J. Nieuwenhuys, and J. A. Mydosh	
Effects of disorder on alkali-doped C ₆₀ photoemission and Raman spectra	15 491
S. J. Chase, M. G. Mitch, J. S. Lannin, and C. G. Olson	
Effective single-particle potentials for MnO in light of interatomic magnetic interactions: Existing theories and perspectives	15 496
I. V. Solovyev and K. Terakura	
One- and two-hole states in the two-dimensional <i>t</i> - <i>J</i> model via series expansions	15 508
C. J. Hamer, Zheng Weihong, and J. Oitmaa	
Vortex, Skyrmion, and elliptical domain-wall textures in the two-dimensional Hubbard model	15 520
G. Seibold	
Thermal and dynamical properties of the two-band Hubbard model compared with FeSi	15 528
Kentaro Urasaki and Tetsuro Saso	
Theory of temperature-dependent angle-resolved-photoemission spectrum of heavy-fermion semiconductors	15 534
Peter S. Riseborough	
Corrections to density-functional theory band gaps	15 548
Kurt A. Johnson and N. W. Ashcroft	
Dynamics of electronic relaxation in characteristic x-ray radiation processes in wide-gap insulators: Separation of luminescence from Raman scattering	15 557
Hideo Mizouchi	
Transition from the adiabatic to the sudden limit in core-electron photoemission	15 565
Lars Hedin, John Michiels, and John Inglesfield	

<i>Ab initio</i> calculation of the lithium-tin voltage profile	15 583
I. A. Courtney, J. S. Tse, Ou Mao, J. Hafner, and J. R. Dahn	
Transmission and absorption properties of two-dimensional metallic photonic-band-gap materials	15 589
Lie-Ming Li, Zhao-Qing Zhang, and Xiangdong Zhang	
Pairing of vibronic small excitons due to enhanced polarizability in a crystalline polarizable nonmetallic medium	15 595
Mladen Georgiev and Jai Singh	
Ground state of orthorhombic RbC_{60} : A high-field electron-spin-resonance investigation	15 603
M. Bennati, R. G. Griffin, S. Knorr, A. Grupp, and M. Mehring	
Semiconductors I: bulk	
Vibrational modes of carbon acceptors and hydrogen-carbon pairs in semi-insulating InP doped using CCl_4	15 609
B. R. Davidson, R. C. Newman, and C. C. Button	
Evidence for two distinct defects contributing to the <i>H4</i> deep-level transient spectroscopy peak in electron-irradiated InP	15 614
B. Massarani, F. G. Awad, M. Kaaka, and R. Darwich	
Electronic structure of CoSb_3 : A narrow-band-gap semiconductor	15 620
J. O. Sofo and G. D. Mahan	
Theoretical study on the nature of band-tail states in amorphous Si	15 624
P. A. Fedders, D. A. Drabold, and S. Nakhmanson	
Defect studies in as-deposited and processed nanocrystalline Si/SiO_2 structures	15 632
S. M. Prokes, W. E. Carlos, S. Veprek, and Ch. Ossadnik	
Semiconductors II: surfaces, interfaces, microstructures, and related topics	
<i>Ab initio</i> studies of the (111) and $(\bar{1}\bar{1}\bar{1})$ surfaces of cubic BN: Structure and energetics	15 636
K. Kádas, G. Kern, and J. Hafner	
Instability of two-dimensional layers in the Stranski-Krastanov growth mode of Ge on Si(111)	15 647
Alexander A. Shklyae, Motoshi Shibata, and Masakazu Ichikawa	
Spin-polarization spectroscopy in rectangular GaAs quantum wires	15 652
T. Sogawa, H. Ando, S. Ando, and H. Kanbe	
Confinement-induced reduction of the effective exchange parameters in semimagnetic semiconductor nanostructures	15 660
A. K. Bhattacharjee	
Photon drag current due to spin-flip transitions of electrons in nonsymmetric quantum wells	15 666
F. T. Vasko and O. Keller	
<i>p</i> -type δ -doping quantum wells and superlattices in Si: Self-consistent hole potentials and band structures	15 675
A. L. Rosa, L. M. R. Scolfaro, R. Enderlein, G. M. Sipahi, and J. R. Leite	
Long-wavelength collective excitations in a two-dimensional spin-polarized electron gas: A phenomenological theory	15 688
D. C. Marinescu and J. J. Quinn	
Density of states of a two-dimensional electron gas in a nonquantizing magnetic field	15 698
A. M. Rudin, I. L. Aleiner, and L. I. Glazman	
Quasiparticles in fractional quantum Hall effect edge theories	15 704
R. A. J. van Elburg and K. Schoutens	
Topological degeneracy of quantum Hall fluids	15 717
X.-G. Wen and A. Zee	
Dielectric response of a nondegenerate electron gas in semiconductor nanocrystallites	15 729
E. van Faassen	
Optical properties versus growth conditions of CdTe submonolayers inserted in ZnTe quantum wells	15 736
Vincent Calvo, Noël Magnea, Thierry Taliercio, Pierre Lefebvre, Jacques Allègre, and Henry Mathieu	

Confined optical modes in photonic wires	15 744
A. Kuther, M. Bayer, T. Gutbrod, A. Forchel, P. A. Knipp, T. L. Reinecke, and R. Werner	
Ion-induced crystal damage during plasma-assisted MBE growth of GaN layers	15 749
V. Kirchner, H. Heinke, U. Birkle, S. Einfeldt, D. Hommel, H. Selke, and P. L. Ryder	
Collective intersubband transitions in quantum wells: A comparative density-functional study	15 756
C. A. Ullrich and G. Vignale	
Envelope-function equation and variational method for superlattices	15 766
B. W. Kim	
Singlet exciton relaxation in isolated polydiacetylene chains studied by subpicosecond pump-probe experiments	15 777
B. Kraabel, M. Joffe, C. Lapersonne-Meyer, and M. Schott	
Zero-bias anomaly in asymmetric contacts	15 789
Michael Reizer	
All-porous silicon-coupled microcavities: Experiment versus theory	15 794
L. Pavesi, G. Panzarini, and L. C. Andreani	
P_{b1} interface defect in thermal (100)Si/SiO ₂ : ²⁹ Si hyperfine interaction	15 801
A. Stesmans, B. Nouwen, and V. V. Afanas'ev	

Surface physics, low-dimensional systems, and related topics

Dissolution modes of Fe/Cu and Cu/Fe deposits	15 810
S. Delage, B. Legrand, F. Soisson, and A. Saúl	
Nonlinear optical response of noble metals determined from first-principles electronic structures and wave functions: Calculation of transition matrix elements	15 821
T. A. Luce and K. H. Bennemann	
Driving-voltage-induced mechanical force oscillations in metal quantum-point contacts	15 827
Alexandre M. Zagoskin	
Transmission of low-energy (≤ 10 eV) H ⁺ and D ⁺ ions through ultrathin rare-gas films	15 832
Markus B. Raschke and Theodore E. Madey	
Contribution of the excitation of conduction band electrons to the kinetic electron emission induced by slow ions in metals	15 838
J. I. Juaristi, M. Rösler, and F. J. García de Abajo	
Simulations of energetic beam deposition: From picoseconds to seconds	15 847
Joachim Jacobsen, B. H. Cooper, and James P. Sethna	
Anomalous pinning behavior in an incommensurate two-chain model of friction	15 866
Takaaki Kawaguchi and Hiroshi Matsukawa	
Chemistry and kinetics of the GaN formation by plasma nitridation of GaAs: An <i>in situ</i> real-time ellipsometric study	15 878
M. Losurdo, P. Capezzuto, G. Bruno, and E. A. Irene	
Resolving the atomic structure of supported nanometer-size Au clusters	15 889
D. Lovall, M. Buss, R. P. Andres, and R. Reifengerger	
Giant field fluctuations and anomalous light scattering from semicontinuous metal films	15 897
F. Brouers, S. Blacher, and Andrey K. Sarychev	
Subsurface bonding of hydrogen in niobium: A molecular-dynamics study	15 904
Aldo H. Romero, Ivan K. Schuller, and Ricardo Ramirez	

COMMENTS

Comment on "Odd-parity excitons in semiconductor superlattices"	15 909
Stephan Glutsch	

CONTENTS - *Continued*

PHYSICAL REVIEW B

THIRD SERIES, VOLUME 58, NUMBER 23

15 DECEMBER 1998-I

Reply to “Comment on ‘Odd-parity excitons in semiconductor superlattices’ ”	15 911
K. Bott, J. Hader, T. Meier, D. Brinkmann, S. W. Koch, and P. Thomas	

Errata

Erratum: Single-electron tunneling at high temperature [Phys. Rev. B 56 , 1848 (1997)]	15 912
P. Joyez and D. Esteve	
Erratum: Diffusion on a stepped substrate: Collective diffusion in the Langmuir gas model [Phys. Rev. B 56 , 2166 (1997)]	15 912
J. Merikoski and S. C. Ying	
Erratum: Effect of adsorption on surface roughening [Phys. Rev. B 56 , R10 067 (1997)]	15 913
V. P. Zhdanov and B. Kasemo	
Erratum: Lagrange-multiplier method in correlated-electron systems: Exact diagonalization study [Phys. Rev. B 57 , 6208 (1998)]	15 913
Takashi Yanagisawa	
Erratum: Formation of a bilayer ordered surface alloy Mn/Ag(001) [Phys. Rev. B 57 , 8823 (1998)]	15 913
Wondong Kim, Wookje Kim, S.-J. Oh, J. Seo, J.-S. Kim, H.-G. Min, and S.-C. Hong	
Erratum: Diffusion and carrier recombination by interstitials in silicon [Phys. Rev. B 57 , 9727 (1998)]	15 914
Walter A. Harrison	

Cumulative Author Index	15 915
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